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Docket: P910351

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hsu et al.	1
U.S. Serial No: 10/627,000	/ / / Examiner: Schillinger, Laura M.
Filed: July 25, 2003	/ /
For: METHOD FOR FORMING NON- VOLATILE MEMORY CELL WITH LOW-TEMPERATURE-FORMED DIELECTRIC BETWEEN WORD AND BIT LINES, AND NON-VOLATILE MEMORY ARRAY INCLUDING SUCH MEMORY CELLS	/ Group Art: 2813 / / / / / / / / / / / / / / / / / / /
•	Kenton R. Mullins, Reg. No. 36,331

Mail Stop Non-Fee Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

Sir:

Responsive to the Examiner's Office Action of November 24, 2004, Applicants hereby elect without traverse the invention of Group I as outlined by the Examiner, comprising Claims 1-13 which pertain to a method including forming an electron trapping layer.

Applicants respectfully submit that the application is now in condition for a first action on the merits, and request that such be done at an early date. Should the Examiner believe that a telephone conference with Applicants' representative would be helpful to advance the prosecution of the application, he is invited to contact the undersigned with any questions.

Respectfully submitted,

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